

# CAD for VLSI Design - II

## Lecture 1

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# About the course

- Advanced Digital Fundamentals
  - Transistor Theory
  - Arithmetic Circuits Design
  - Pipelining fundamentals
  - Case study of a pipelined superscalar processor
  - ASIC Design flow

The Course Starts Here

Transistor Theory


# History: Transistor Revolution

- **1947:** Transistor by J. Bardeen, W. Brattain at Bell Labs.
- **1949:** Bipolar transistor by W. Shockley.
- **1956:** First bipolar digital logic gate by Harris
- **1958:** First monolithic IC by Jack Kilby at Texas Instruments.
- **1960:** First commercial logic gate IC from Fairchild.
- **1962:** TTL – the *first IC revolution*
- **1974:** ECL – first sub-nanosecond digital gates.

Tech.	Year	Approx. # trans./chip	Typical Products
Devices	1950-60	1	Transistors and diode
SSI	1960-65	10	Logic gates, latches, etc.
MSI	1965-70	100 - 1K	Counters, adders, etc.
LSI	1970-80	1K - 20K	8-bit $\mu$ Proc., ROM, RAM, ...
VLSI	1980-85	20K - 500K	16-bit $\mu$ Proc., peripherals, ...
ULSI	1986-	> 500K	32-bit $\mu$ Proc., DSPs, ASICs, ...

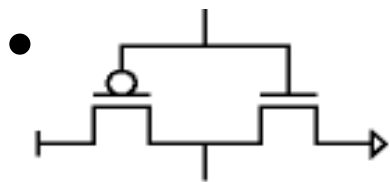


# MOSFET Technology

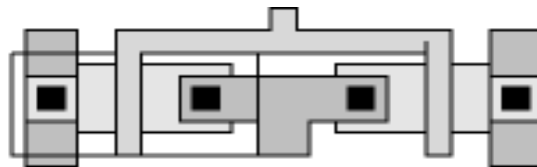
- **1925**: Basic principle behind MOSFETs (IGFET) – independently proposed by J. Lilienfeld (Canada) in **1925** and O. Heil (England) in **1935**.
- **1963**: CMOS gate – F. Wanlass and C. Sah. Plagued with manufacturing problems.
- **1960's**: PMOS for calculators.
- **1972**: Intel 4004 – the *second IC revolution*. NMOS used for speed.
- **1980s**: CMOS – dominant technology of the information age because of lower power and ease of design.
- BiCMOS, SiGe, GaAs, ...
- Cu interconnect, low-K dielectric, SOI, ... 

# CMOS Technology

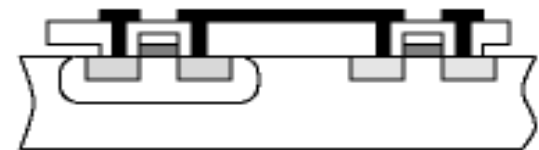
- **CMOS** – **C**omplementary **M**etal **O**xide **S**emiconductor.
- **MOSFET** – a sandwich structure of **M**etal, **O**xide and **S**emiconductor. Modern processes use *polysilicon* instead of metal for gate - originally called **IGFET**.



*Schematic*



*Layout (top view)*



*Chip Cross section (side view)*

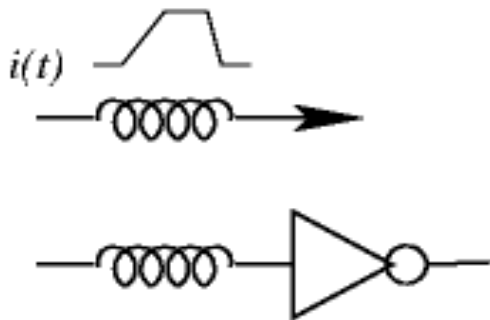
# Technology Roadmap: ITRS 2001

Year	2001	2003	2006	2010	2013	2016
<i>Feature size (nm)</i>	130	90	53	32	22	16
<i>Mtrans/cm<sup>2</sup></i>	38	61	122	309	617	1235
<i>DRAM bits (Gbits)</i>	0.512	1	2	8	32	64
<i>Chip size (mm<sup>2</sup>)</i>	280	280	280	280	280	280
<i>Signal pins / chip</i>	1024	1024	1024	1280	1408	1472
<i>Power/GND pins/chip</i>	2048	2048	2048	2560	2816	2944
<i>Clock rate (GHz)</i>	1.7	3.1	5.6	11.5	19.3	28.8
<i>Wiring levels</i>	7	8	9	10	10	10
<i>Power supply (V)</i>	1.1	1.0	0.9	0.6	0.5	0.4
<i>High-perf power (W)</i>	130	150	180	218	251	288
<i>Battery power (W)</i>	2.4	2.8	3.5	3.0	3.0	3.0

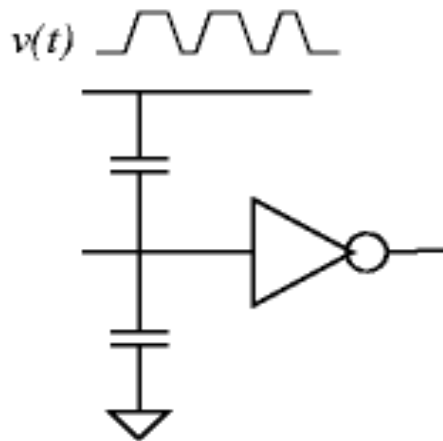


# Reliability: Noise in Digital ICs

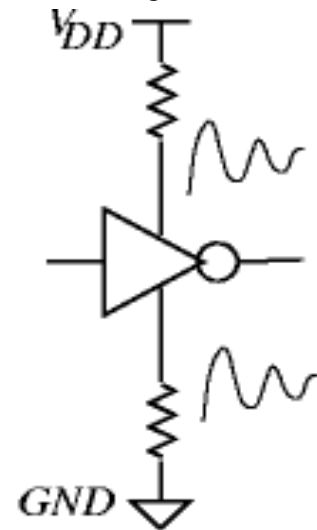
- **Noise** – unwanted variations of voltage and currents at nodes in a logic circuit.
- Most noise in a digital system is internally



Inductive coupling



Capacitive coupling



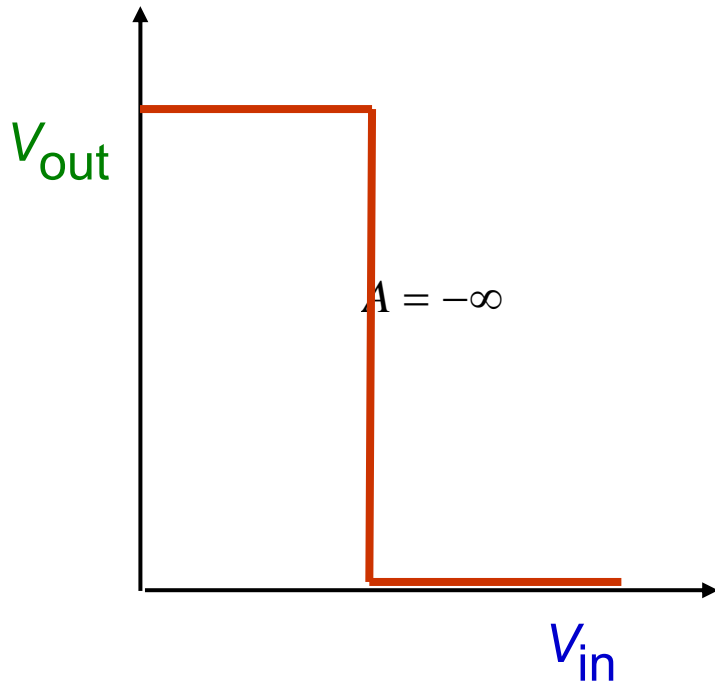
Power & Ground noise



# Noise Immunity

- *Noise immunity* expresses the ability of the system to process and transmit information correctly in the presence of noise  $\Rightarrow$  *reject a noise source instead of overpowering it*
- For a given set of noise sources, the minimum signal swing necessary for the system to be operational can be derived.
- The signal swing (and the noise

# The Ideal Inverter



Gain in the transition region:  $A = -\infty$

$$R_{in} = \infty$$
$$R_{out} = 0$$

$V_M = V_{dd}/2$  (middle of the logic swing)

$$NM_H = NM_L = V_{dd}/2$$

Fanout =

# Questions and Answers

**Thank You**